

## Features

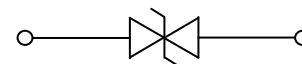
- 150W peak pulse power ( $t_p = 8/20\mu s$ )
- Bidirectional configurations
- Protects one I/O port
- Low clamping voltage
- Low Leakage current
- ESD-immunity acc. IEC 61000-4-2  $\pm 30kV$  contact  $\pm 30kV$  air
- IEC 61000-4-4 (EFT) 40A (5/50ns)



DFN1006

## Applications

- Cell Phone
- PDA
- Notebook
- Digital Cameras
- Portable Instrumentation
- Audio and video equipment



Schematic Diagram

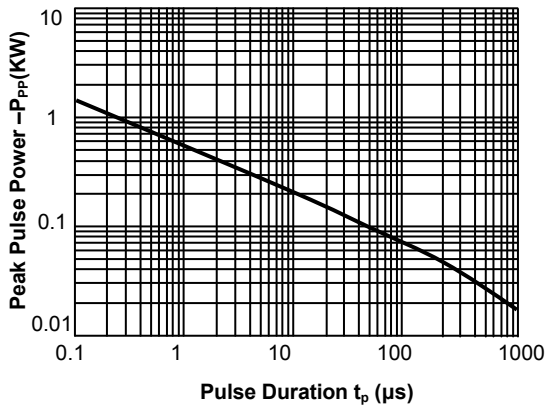
## Absolute Maximum Ratings ( $T_A = 25^\circ C$ unless otherwise specified)

Parameter	Symbol	Max.	Unit
Peak Pulse Power ( $T_p = 8/20\mu s$ )	$P_{PP}$	150	W
Peak Pulse Current ( $t_p = 8/20\mu s$ )	$I_{PP}$	9.4	A
Junction Temperature	$T_J$	-55 To +125	$^\circ C$
Storage Temperature	$T_{STG}$	-55 To +150	$^\circ C$

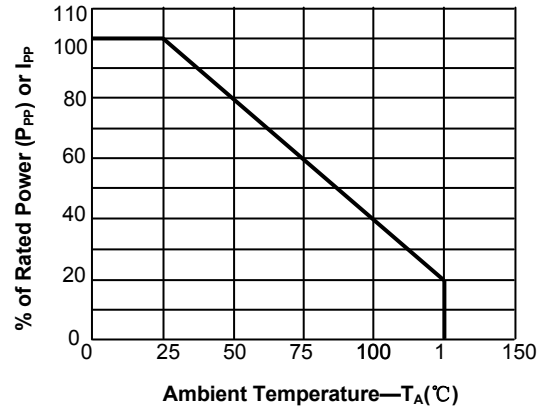
## Electrical Characteristics ( $T_A = 25^\circ C$ unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Reverse Stand-Off Voltage	$V_{RWM}$	-	-	-	5	V
Reverse Breakdown Voltage	$V_{BR}$	$I_T = 1mA$	5.6	6.8	-	V
Reverse Leakage Current	$I_R$	$V_R = 5V$	-	-	1	$\mu A$
Clamping Voltage	$V_C$	$I_{PP} = 5A, T_p = 8/20\mu s$	-	-	11.6	V
	$V_C$	$I_{PP} = 9.4A, T_p = 8/20\mu s$	-	-	18.6	V
Junction Capacitance	$C_J$	$V_R = 0V, f = 1MHz$	-	15	-	pF

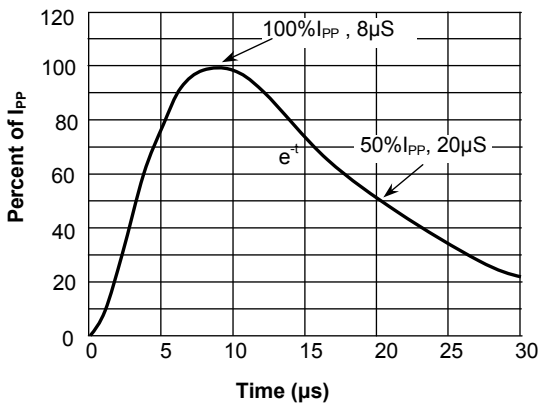
**Typical Characteristic Curves**



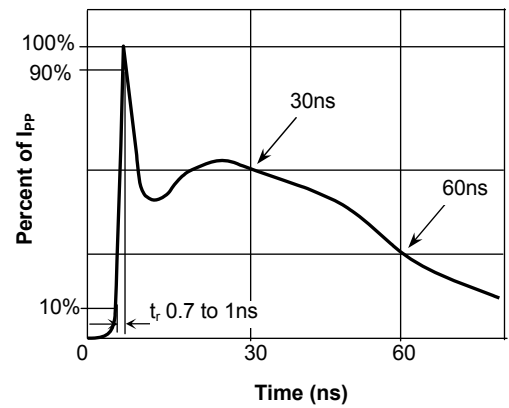
**Fig.1 Peak Pulse Power Rating Curve**



**Fig.2 Pulse Derating Curve**



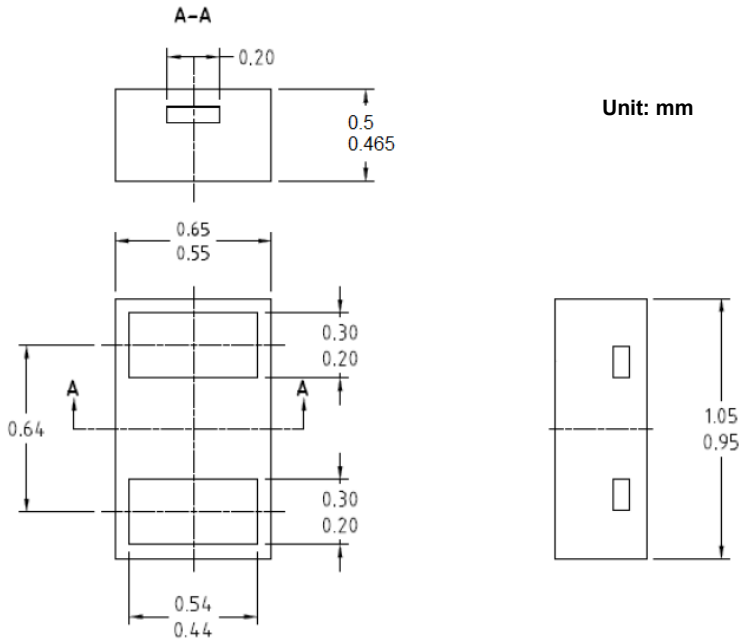
**Fig.3 Pulse Waveform-8/20μs**



**Fig.4 Pulse Waveform-ESD(IEC61000-4-2)**

**Product Dimensions**

**DFN1006**



**Order Information**

Device	Package	Marking	Carrier	Quantity	HSF Status
GSEZ5B159	DFN1006	C	Tape & Reel	10,000pcs / Reel	RoHS compliant